Receipt date: 12/09/2004

101/8518945 DT05 Rec'd PCT/PF0 0 9 DEC 2004

			,
Collections for form 1440 (DTO	C	omplete n Anown	
Substitute for form 1449/PT0	Application Number		
INFORMATION DISCLOSURE	Filing Date		
	First Named Inventor	Yoshihiro ITO	
STATEMENT BY APPLICANT	Art Unit		
(Use as many sheets as necessary)	Examiner Name		
Sheet 1 of 2	Attorney Docket Number	36856.1310	

U.S. PATENT DOCUMENTS					
Examiner Cite		Publication Date	Name of Patentee or	Pages, Columns, Lines, Where	
Initials*	No.1	Number-Kind Code ^{2(if known)}	MM -YYYY	Applicant of Cited Document	Relevant Passages or Relevant Figures Appear
					,,,,,,

		FO	REIGN PATEN	T DOCUMENTS		
Examine r Initials*	Cite No.1	Foreign Patent Document Country Code ³ Number-Kind Code ⁵ (if known)	Publication Date MM -YYYY	Country of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Le
/TN/	1	JP 2002-326895 (English abstract and machine translation)	11/2002	JAPAN		X
/TN/	2	JP 2001-244464 (English abstract and machine translation)	09/2001	JAPAN		X
/TN/	3	JP 2000-150900 (English abstract and machine translation)	05/2000	JAPAN		X
/TN/	4	JP 2002-319682 (English abstract and machine translation	10/2002	JAPAN		X
/TN/	5	JP 10-306372 (English abstract and machine translation	11/1998	JAPAN		X
/TN/	6	EP 1 134 811	09/2001	EPO	1	х
/TN/	7	JP 05-171435 (English abstract and machine translation	07/1993	JAPAN		x
/TN/	8	JP 2001-144328 (English abstract and machine translation	05/2001	JAPAN		X
						<u> </u>

^{*}Examiner: Initial if reference considered, whether of not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered, include copy of this form with next communication to applicant.

Applicant unique citation designation number (optional). *See Kind Codes of USPTO Patent documents at www.uspto.gov or MPEP 901.04. *Set Enter Office that issued the document by the two-letter code (WIPO Strandard ST.3). *For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. *Skind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. *Applicant is to place a check mark here if English language Abstract is attached. This collection of information is required to obtain or retain a benefit by the public which is to file (and by the USPTQ to process an application Southernial Signature of 1350 SC 122 and 370FR E19 E LINED THROUGH. /TN/

Receipt date: 12/09/2004

1 10 18545 9 44 5 2893

DTO C'd PCT/PTO 0 9 DEC 2004.

Examiner Date	-
Signature Considered	

Substitute for form 1449/PT0		Complete if Known			
Substitute	tor torm 14	149/PIU		Application Number	
INIEO	ВΜΛΤ	ו אסו	ICCI OCUDE	Filing Date	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		First Named Inventor	Yoshihiro ITO		
		Art Unit			
(Use as ma	any sheets a	as necessa	ry)	Examiner Name	
Sheet	2	of	2	Attorney Docket Number	36856.1310
	1	1	•	1	ı

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title Of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
/TN/	9	Yutaka OHYA et al., "THIN FILM TRANSISTOR OF ZnO FABRICATED BY CHEMICAL SOLUTION DEPOSITION", Jpn. J. Appl. Phys., Vol. 40 (2001), pp. 297-298, Part 1, No. 1, January 2001.	
/TN/	10	K. YAMAYA et al., "USE OF HELICON-WAVE EXCITED PLASMA FOR ALUMINUM-DOPED ZnO THIN-FILM SPUTTERING", Appl. Phys. Lett. 72 (2), January 12, 1998, pp. 235-237.	
/TN/	11	S.K. HONG et al., "ZnO AND RELATED MATERIALS: PLASMA-ASSISTED MOLECULAR BEAM EPITAXIAL GROWTH, CHARATERIZATION, AND APPLICATION", Journal of Electronic Materials, Vo. 30, No. 6, 2001, pp. 647-658.	
/TN/	12	Shen ZHU et al., "POLARITY EFFECTS OF SUBSTRATE SURFACE IN HOMOEPITAXIAL ZnO FILM GROWTH", Journal of Crystal Growth 219 (2000), pp. 361-367.	
/TN/	13	Yefan CHEN et al., "MORPHOLOGY EVOLUTION OF ZnO (000 1) SURFACE DURING PLASMA-ASSISTED MOLECULAR-BEAM EPITAXY", Applied Physics Letters, Volume 80, Numbe 8, 02/2002, pp. 1358-1360.	
/TN/	14	Soon-Ku HONG et al., "CONTROL OF POLOARITY OF ZnO FILMS GROWN BY PLASMA-ASSISTED MOLECULAR-BEAM EPITAXY: Zn- AND O-POLAR ZnO FILMS ON Ga-POLAR AND GaN TEMPLATES", Applied Physics Letters, Volume 77, Number 22, 11/2000, pp. 3571-3573.	
_			

Examiner Signature	/Thanh Nguyen/	Date 11/26/2008
O.B. Idian		

^{*}Examiner: Initial if reference considered, whether of not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered, include copy of this form with next communication to applicant.

¹ Applicant unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the LATO to receive the public which is to file (and by the LATO to receive the public which is to file (and by the LATO THEOUGH. /TN/